祥瑞微 CRM Microelectronics

CRMGTU0202A

N-Channel 20V, 1.35mΩ Typ. Power MOSFET

Description

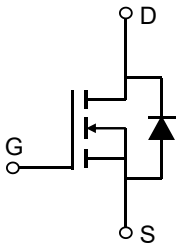
Features

- 20V, 135A

  $R_{DS(ON)}$ Typ = 1.35mΩ @ V_{GS} = 10V

  $R_{DS(ON)}$ Typ = 1.5mΩ @ V_{GS} = 4.5V

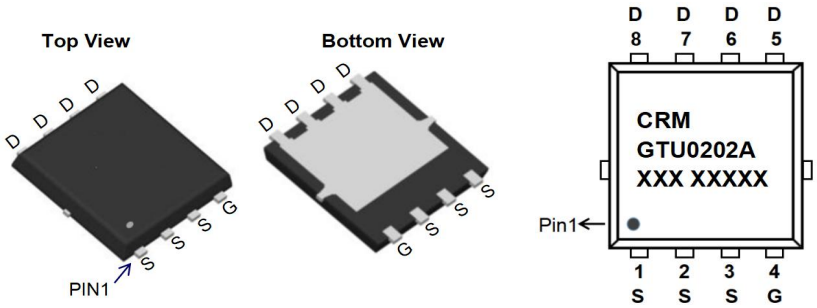
  $R_{DS(ON)}$ Typ = 1.9mΩ @ V_{GS} = 2.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔVds TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMGTU0202A	CRMGTU0202A	PDFN5x6-8L	TAPING	13"	5000	50000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		20	V
V_{GS}	Gate-to-Source Voltage		±12	V
I_D	Continuous Drain Current	T_C = 25°C	135	A
		T_C = 100°C	81	A
I_{DM}	Pulsed Drain Current (1)		540	A
E_{AS}	Single Pulsed Avalanche Energy (2)		169	mJ
P_D	Power Dissipation	T_C = 25°C	62.5	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	0.4	0.7	1	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 30A	-	1.35	1.8	mΩ
		V_{GS} = 4.5V, I_D = 20A	-	1.5	2.0	mΩ
		V_{GS} = 2.5V, I_D = 10A	-	1.9	2.5	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} =10V, f = 1MHz	-	5358	-	pF
C_{oss}	Output Capacitance		-	735	-	pF
C_{rss}	Reverse Transfer Capacitance		-	632	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 4.5V V_{DS} = 10V, I_D = 30A	-	64	-	nC
Q_{gs}	Gate Source Charge		-	12	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	19	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 4.5V, V_{DD} = 10V I_D= 30A, R_{GEN} = 3Ω	-	20	-	ns
t_r	Turn-On Rise Time		-	47	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	117	-	ns
t_f	Turn-Off Fall Time		-	120	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	135	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	540	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	-	22	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	12	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=10V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=26A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

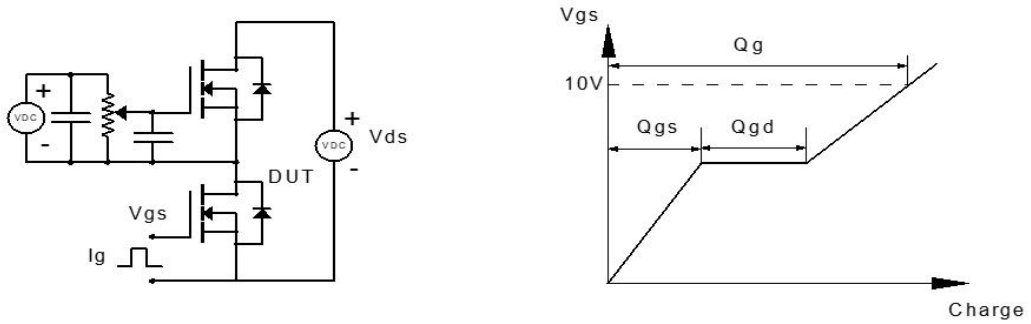


Figure 1: Gate Charge Test Circuit & Waveform

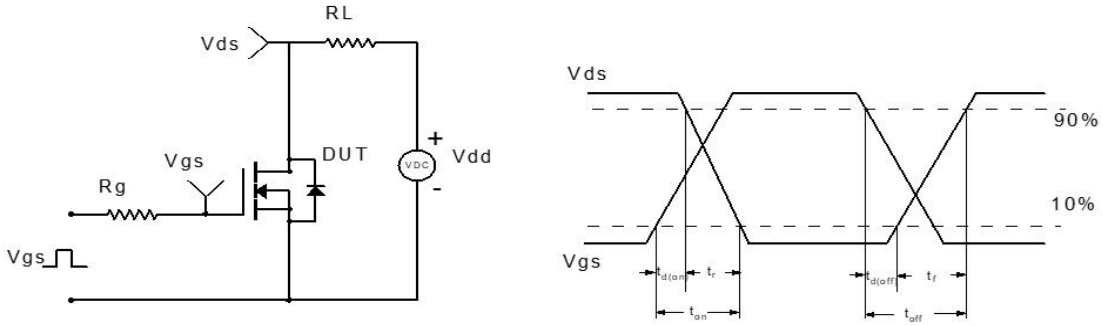


Figure 2: Resistive Switching Test Circuit & Waveform

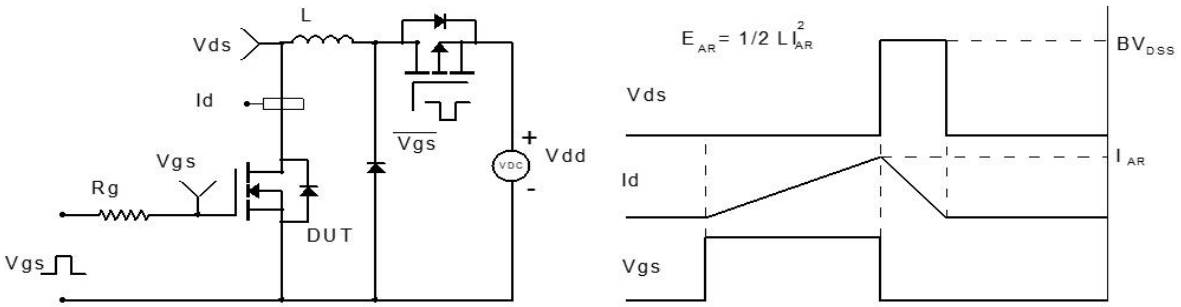


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

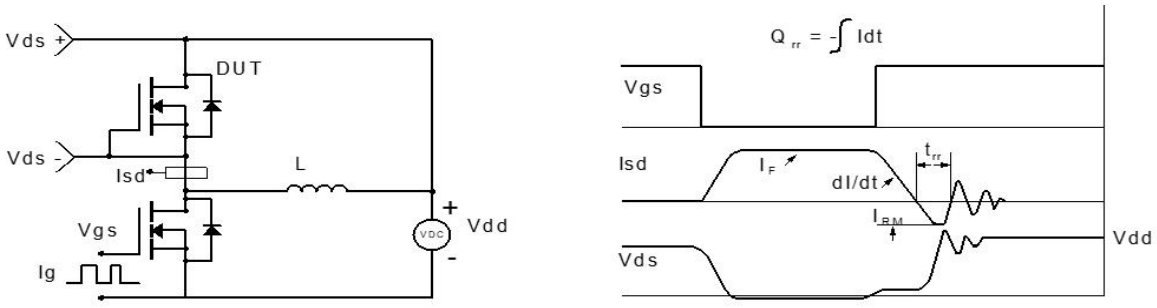
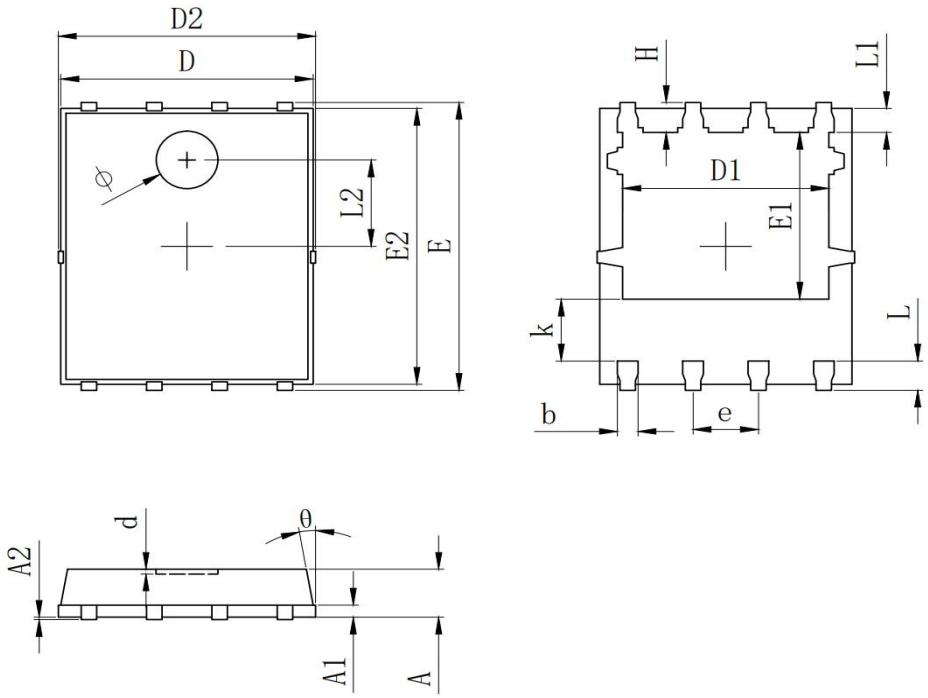


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN5x6-8L)



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0~0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100

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